

FGD4536 360V, PDP IGBT

Features

- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.59\text{ V @ } I_C = 50\text{ A}$
- High Input Impedance
- Fast Switching
- RoHS Compliant

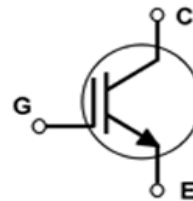
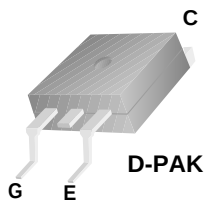
Application

- PDP System



General Description

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description	Ratings	Units
V_{CES}	Collector to Emitter Voltage	360	V
V_{GES}	Gate to Emitter Voltage	± 30	V
$I_C \text{ pulse}(1)^*$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	220	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	125	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	50	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	-	1.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	62.5	$^\circ\text{C/W}$

Notes:

(1) Half Sine Wave, $D < 0.01$, pulse width $< 1\mu\text{sec}$

* I_C pulse limited by max T_J

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGD4536	FGD4536TM	TO252	380mm	16mm	-

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	360	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	-	0.4	-	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	100	μA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	±400	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 250μA, V _{CE} = V _{GE}	2.4	3.3	4.0	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 20A, V _{GE} = 15V	-	1.19	-	V
		I _C = 30A, V _{GE} = 15V	-	1.33	-	V
		I _C = 50A, V _{GE} = 15V, T _C = 25°C	-	1.59	1.8	V
		I _C = 50A, V _{GE} = 15V, T _C = 125°C	-	1.66	-	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	-	1295	-	pF
C _{oes}	Output Capacitance		-	56	-	pF
C _{res}	Reverse Transfer Capacitance		-	43	-	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 200V, I _C = 20A, R _G = 5Ω, V _{GE} = 15V, Resistive Load, T _C = 25°C	-	5	-	ns
t _r	Rise Time		-	20	-	ns
t _{d(off)}	Turn-Off Delay Time		-	41	-	ns
t _f	Fall Time		-	182	-	ns
t _{d(on)}	Turn-On Delay Time	V _{CC} = 200V, I _C = 20A, R _G = 5Ω, V _{GE} = 15V, Resistive Load, T _C = 125°C	-	5	-	ns
t _r	Rise Time		-	21	-	ns
t _{d(off)}	Turn-Off Delay Time		-	43	-	ns
t _f	Fall Time		-	249	-	ns
Q _g	Total Gate Charge	V _{CE} = 200V, I _C = 20A, V _{GE} = 15V	-	47	-	nC
Q _{ge}	Gate to Emitter Charge		-	5.4	-	nC
Q _{gc}	Gate to Collector Charge		-	15	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

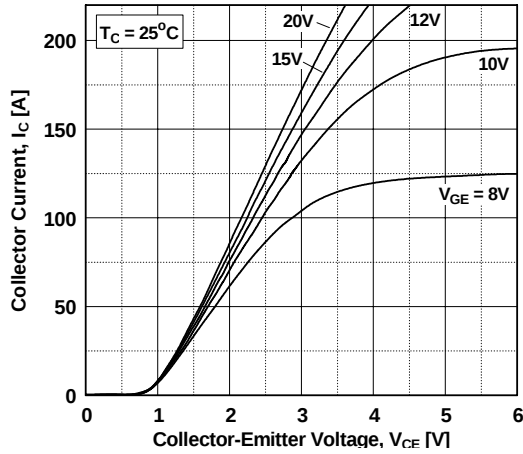


Figure 2. Typical Output Characteristics

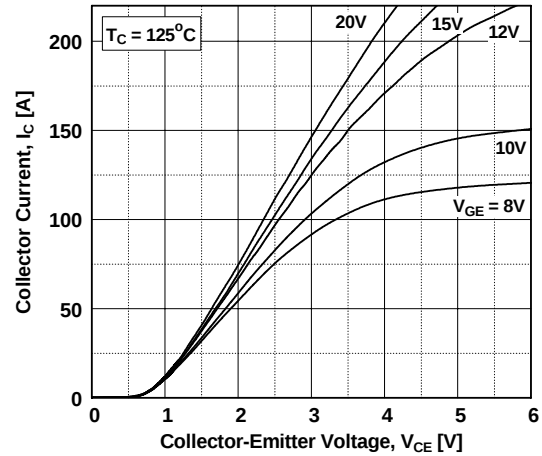


Figure 3. Typical Saturation Voltage Characteristics

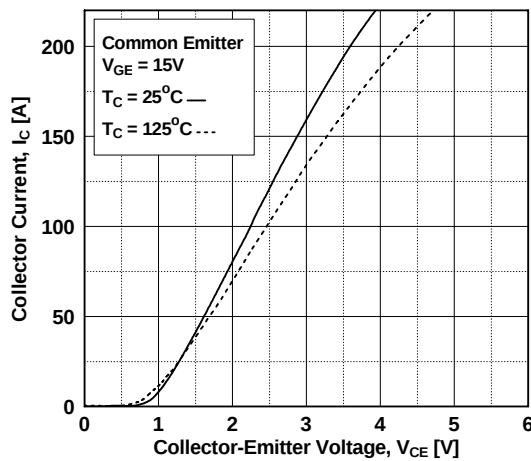


Figure 4. Transfer Characteristics

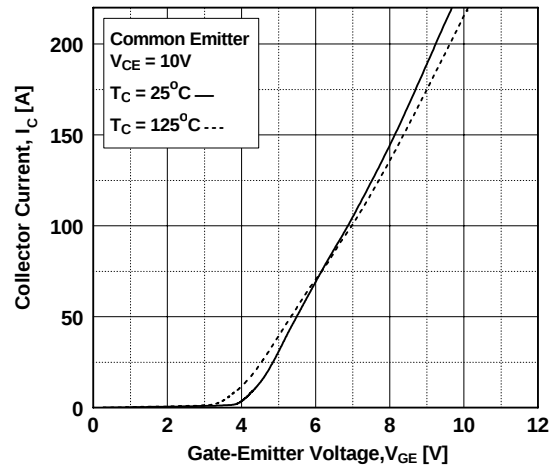


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

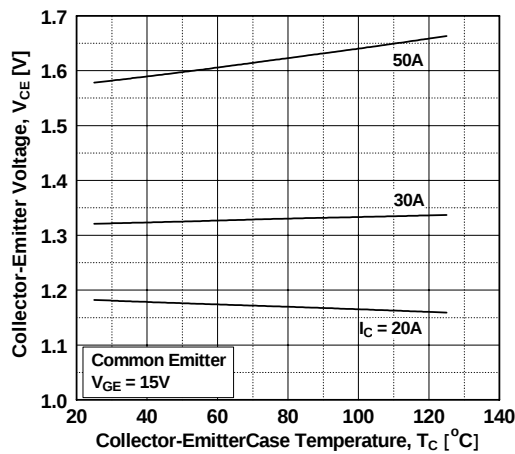
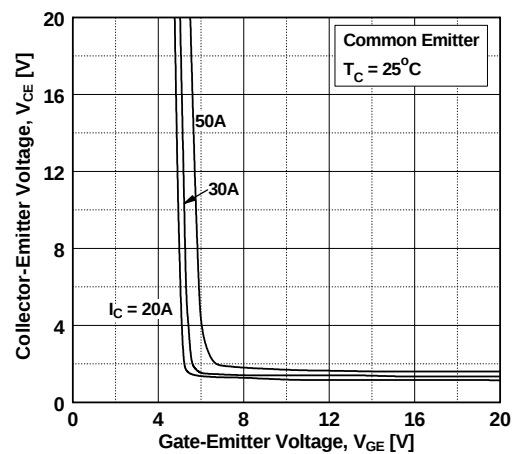


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

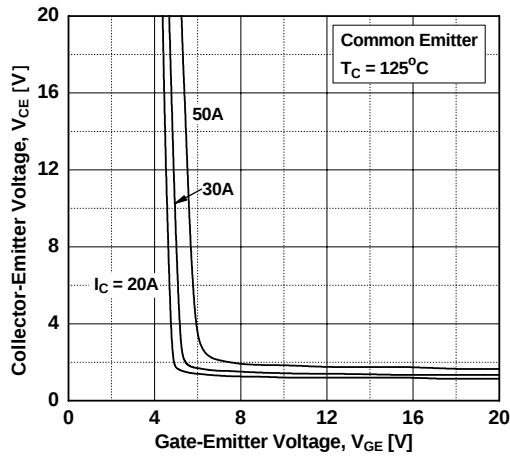


Figure 8. Capacitance Characteristics

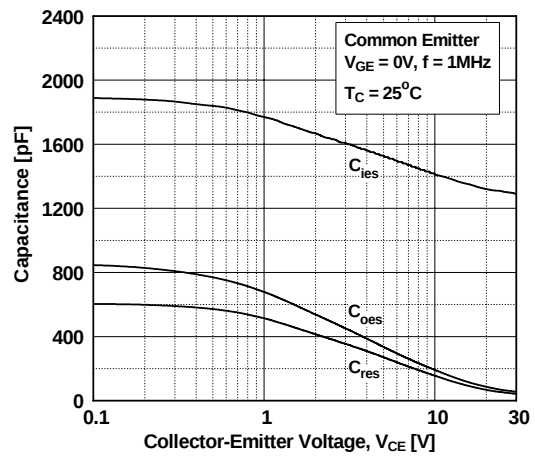


Figure 9. Gate charge Characteristics

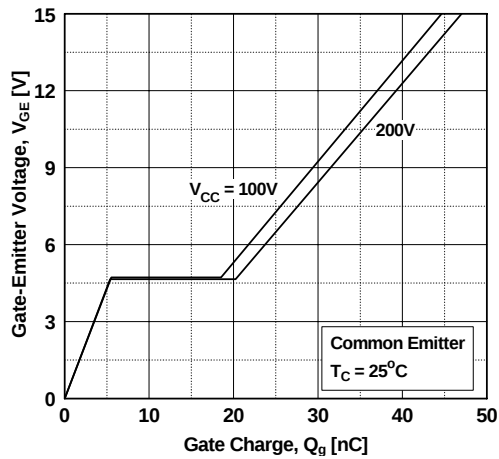


Figure 10. SOA Characteristics

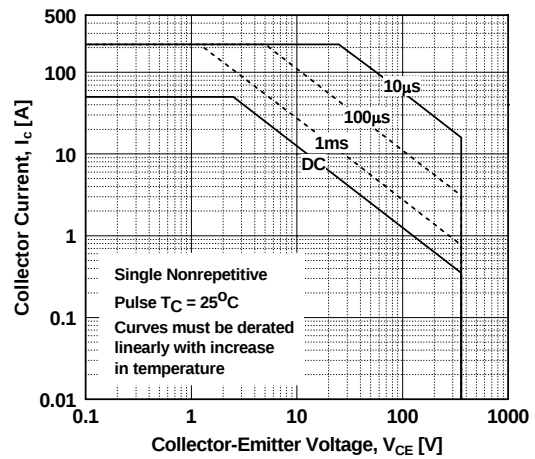


Figure 11. Turn-on Characteristics vs. Gate Resistance

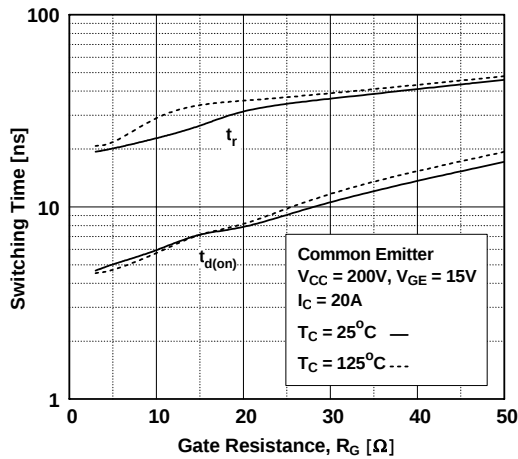
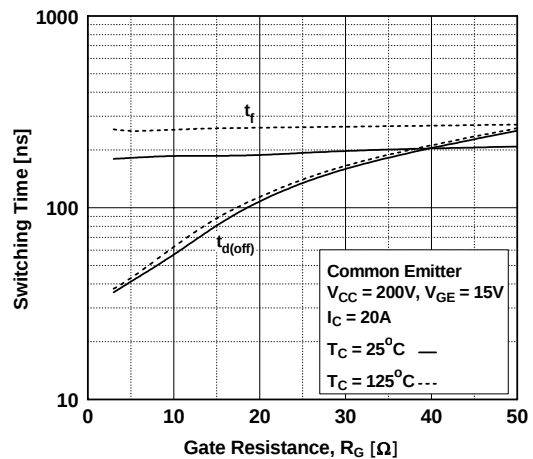


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

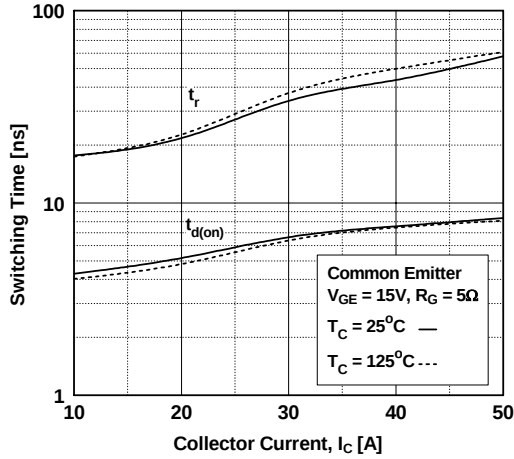


Figure 14. Turn-off Characteristics vs. Collector Current

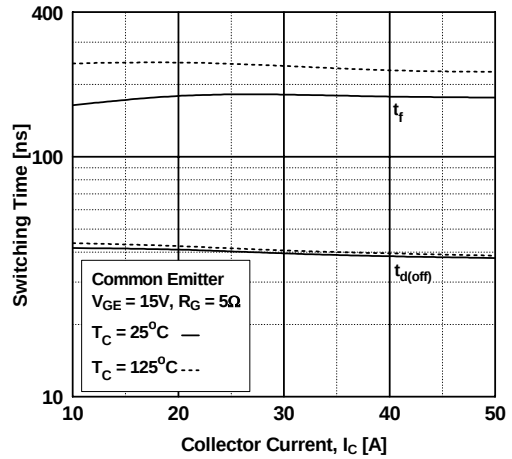


Figure 15. Switching Loss vs. Gate Resistance

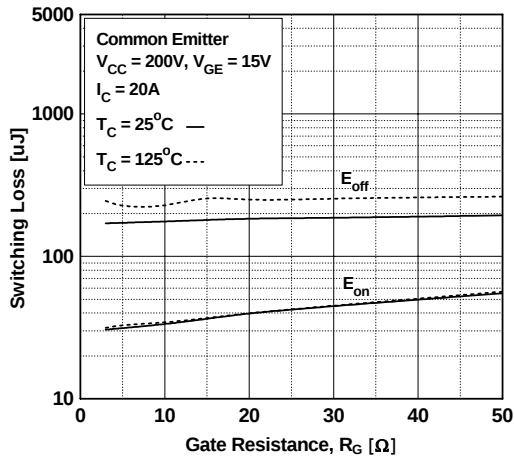


Figure 16. Switching Loss vs. Collector Current

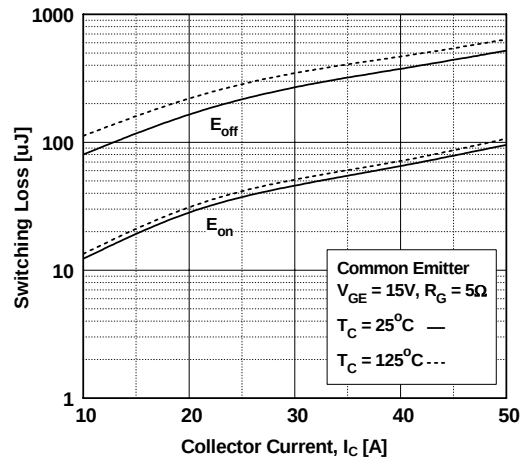
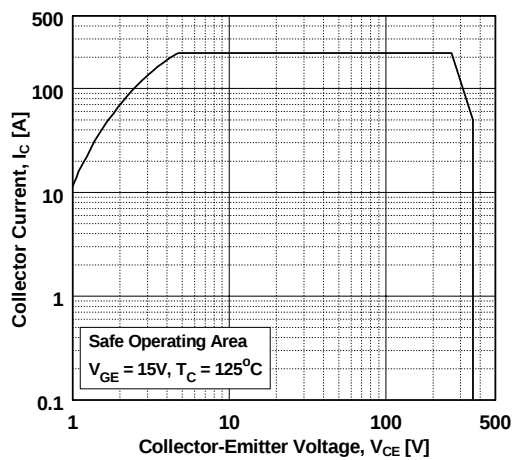
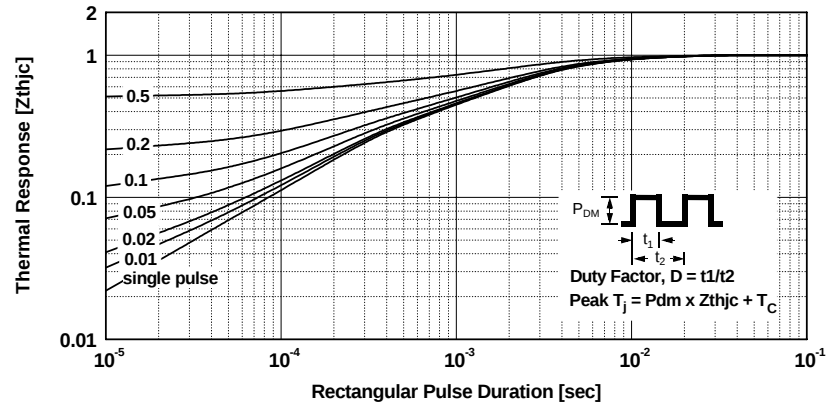


Figure 17. Turn off Switching SOA Characteristics



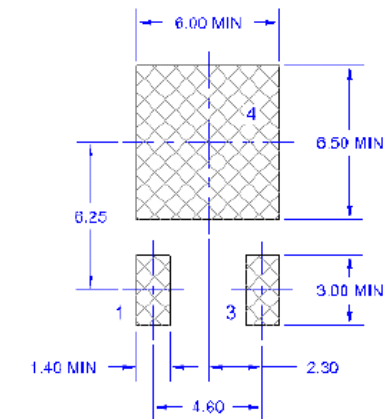
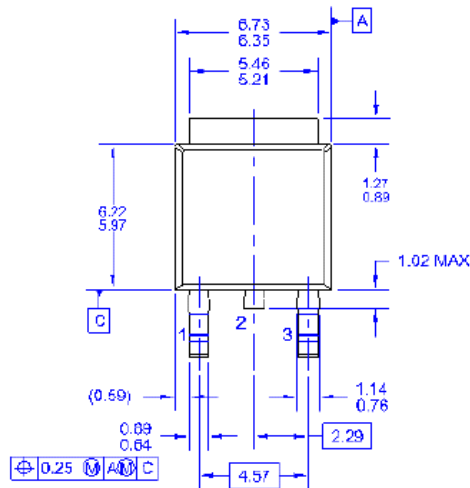
Typical Performance Characteristics

Figure 18. Transient Thermal Impedance of IGBT

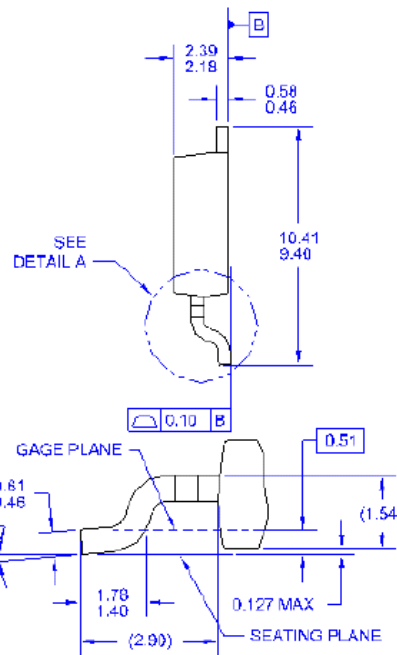
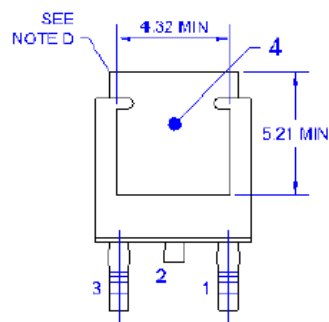


Mechanical Dimensions

D-PAK



LAND PATTERN RECOMMENDATION



- NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE CONFORMS TO JEDEC, TO-252
ISSUE C, VARIATION AA
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER
ASME Y14.5M-1994.
D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED
CORNERS OR EDGE PROTRUSION.
E) PRESENCE OF TRIMMED CENTER LEAD
IS OPTIONAL.
F) DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH AND TIE BAR PROTRUSIONS.
G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
TO220P1003K236-3N.
H) DRAWING NUMBER AND REVISION: MKT-T0252A03REV B

Dimensions in Millimeters

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